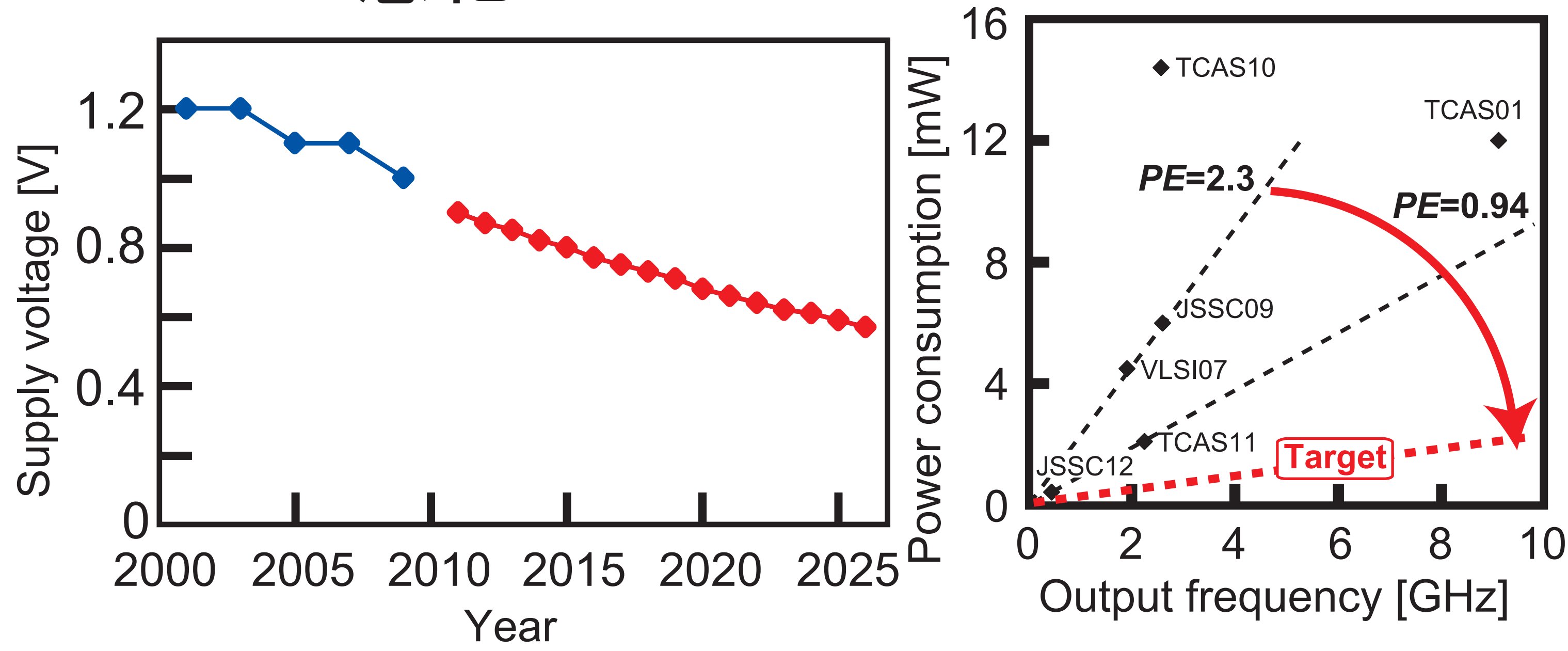


C級動作VCOと注入同期型分周回路を用いた 低電力位相同期回路

目的

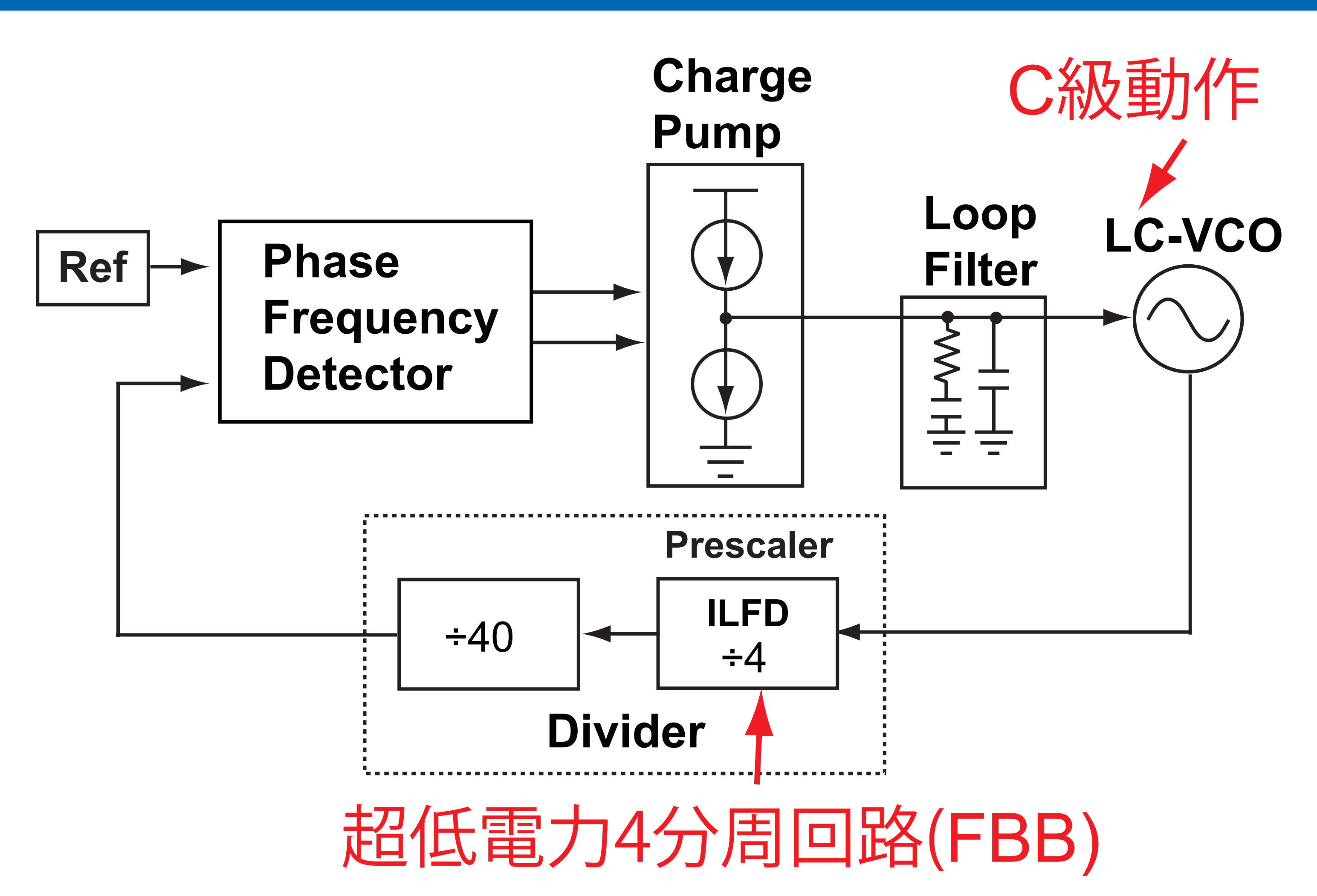
CMOSプロセスの微細化

- 電源電圧低下
- SNR悪化

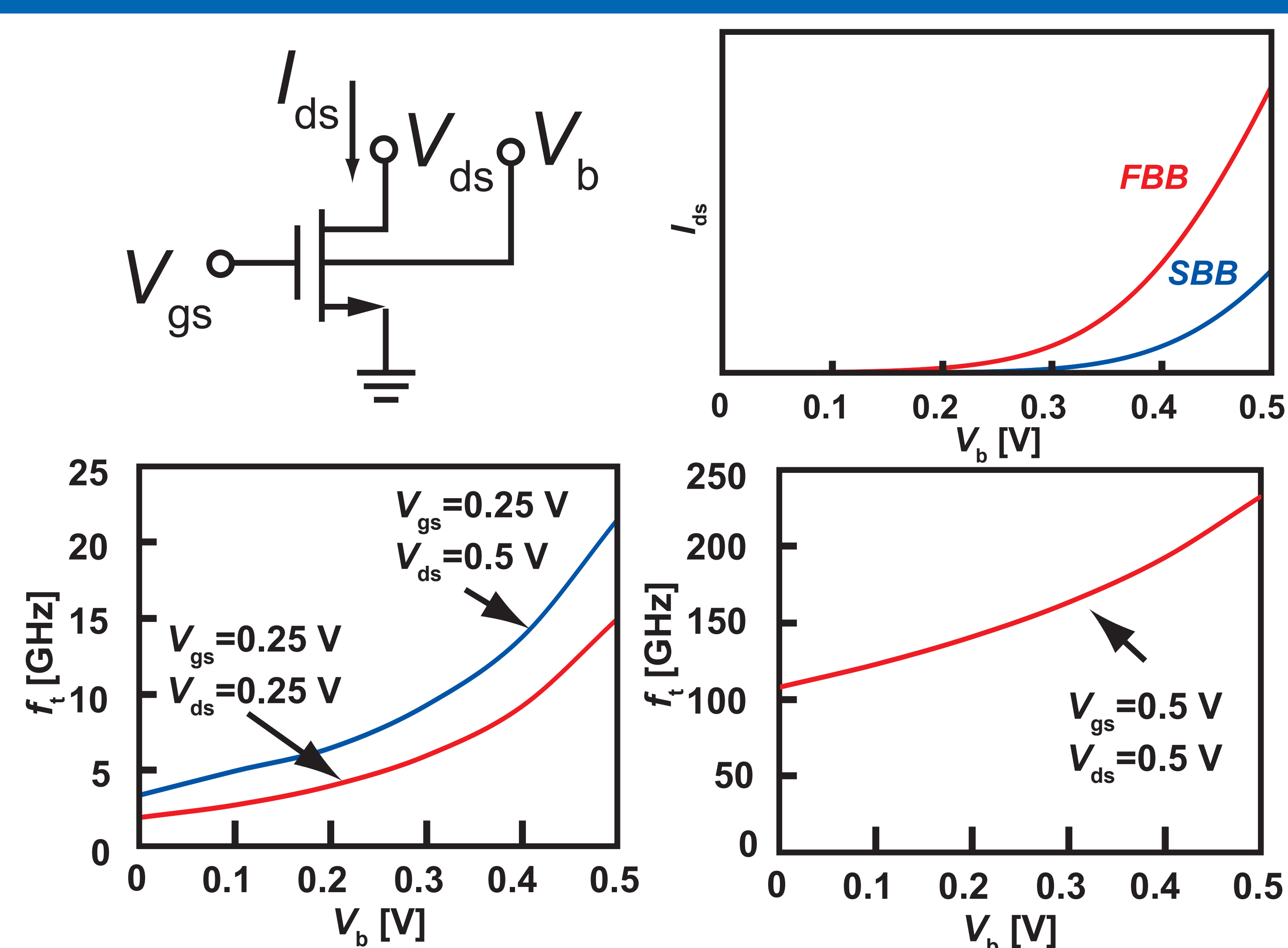


0.5V動作、低電力周波数シンセサイザの実現

提案構成



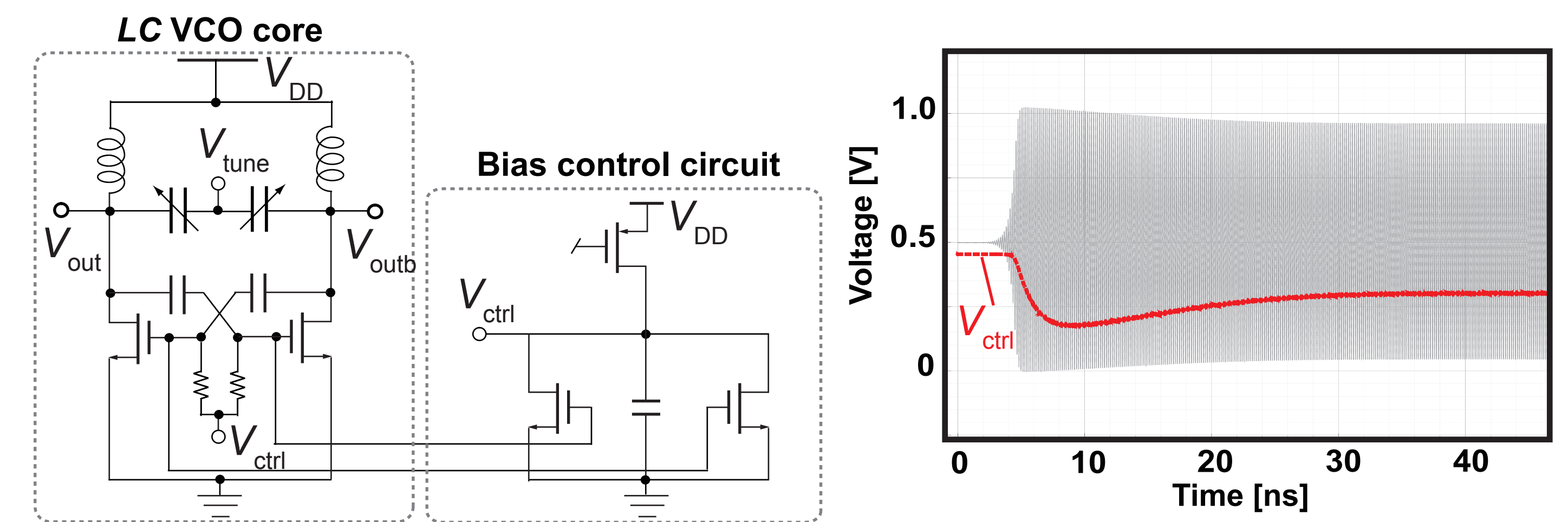
Forward Body Bias (FBB)



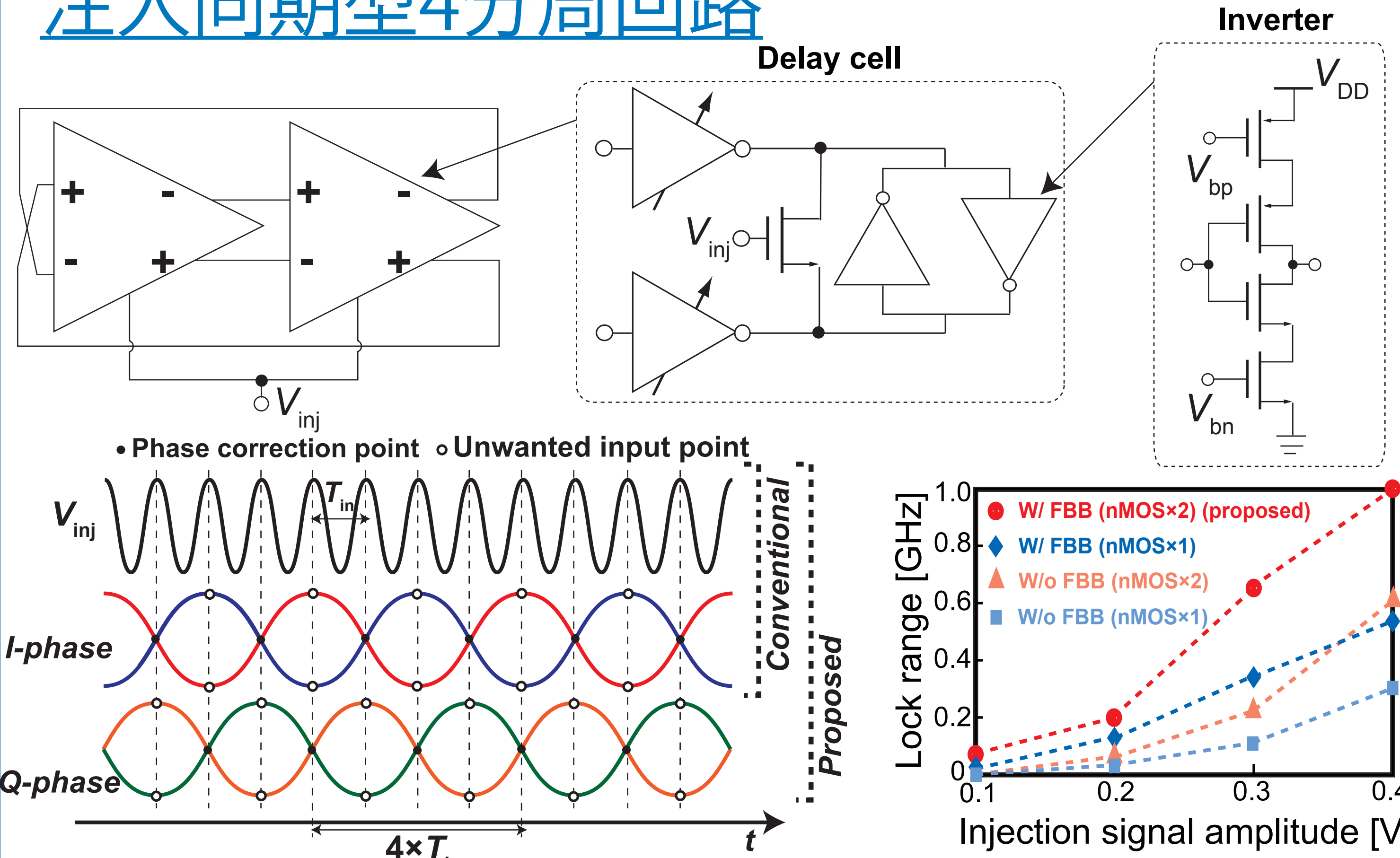
しきい値 ↓ 遮断周波数 ↑
⇒ 低電圧・高周波動作！

回路詳細および測定結果

C級動作VCO

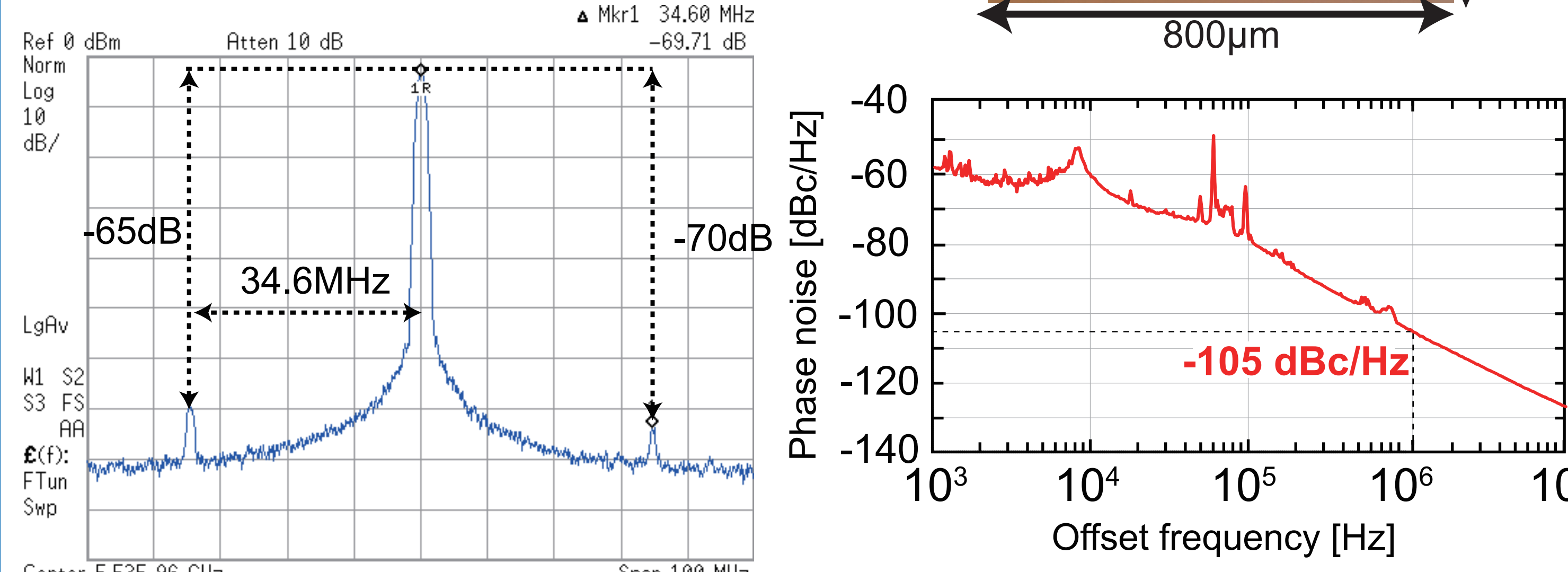
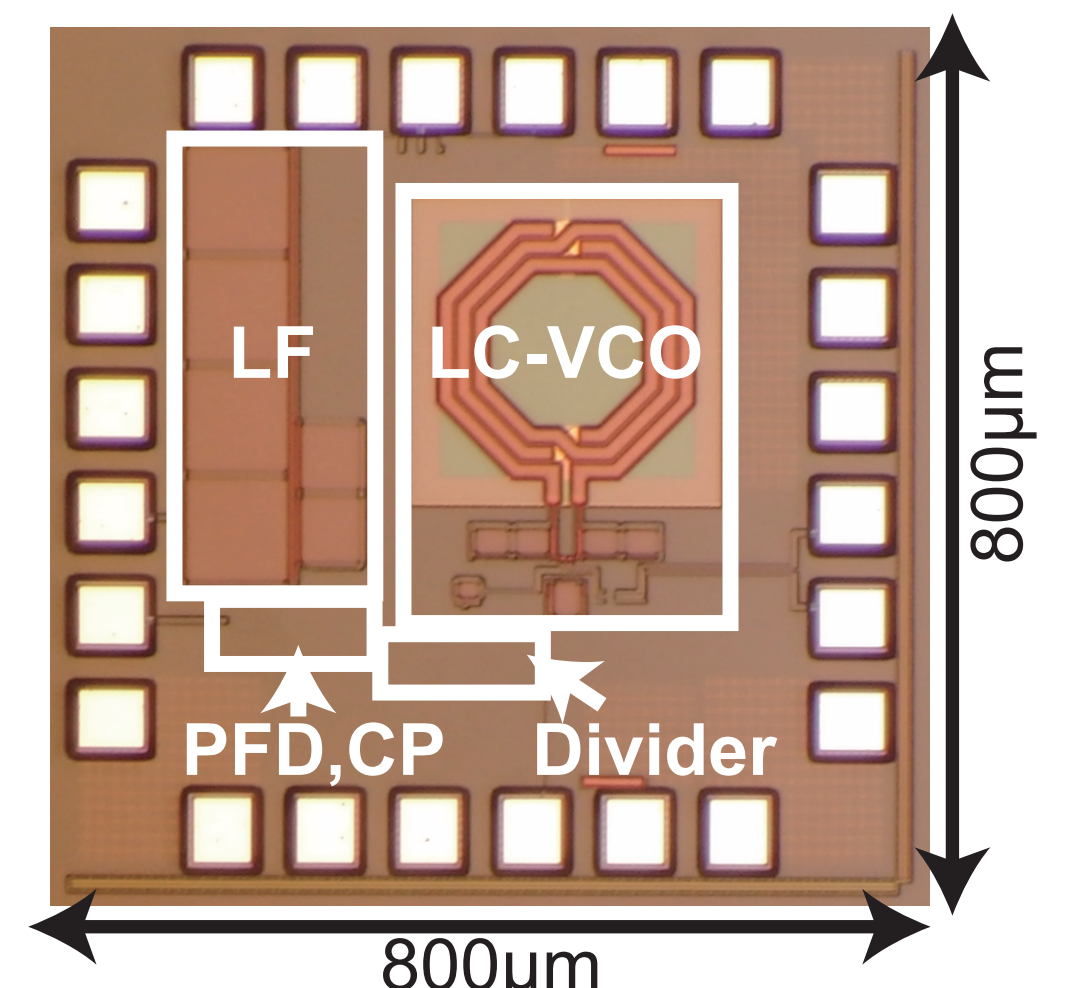


注入同期型4分周回路



測定結果

	Power [mW]
VCO	0.915
FD	0.425
PFD+CP	0.260
Total	1.6



	Tech. [nm]	f _{out} [GHz]	V _{DD} [V]	PN [dBc/Hz]	Power [mW]
This work	65	5.54	0.5	-105	1.6
[1]	180	1.9	0.5	-120	4.5
[2]	180	2.56	0.5	-105	14.4
[3]	90	2.59	0.5/0.65	-113	6.0
[4]	130	9.12	0.5/0.8	-105	12
[5]	90	2.24	0.5	-87	2.1

[1] H.-H. Hsieh, et al., VLSI 2007 [4] C.-Y. Yang, et al., TCAS 2001
[2] C.-T. Lu, et al., TCAS 2010 [5] K.-H. Cheng, et al., TCAS 2011
[3] S.-A. Yu, et al., JSSC 2009

まとめ

- ◆ 0.5V 動作超低電力周波数シンセサイザ
 - ・ C級動作VCO, 超低電力4分周回路 (FBB)
- ◆ 5.5GHz 動作時, 1.6mW 消費電力
⇒ 世界トップレベルパワー効率 (0.29mW/GHz)